FAIRCHILD

74LVT16373 • 74LVTH16373 Low Voltage 16-Bit Transparent Latch with 3-STATE Outputs

General Description

Features

- Input and output interface capability to systems at $5V V_{CC}$
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH16373), also available without bushold feature (74LVT16373)

- Live insertion/extraction permitted
- Power Up/Power Down high impedance provides glitch-free bus loading
- Outputs source/sink –32 mA/+64 mA
- Functionally compatible with the 74 series 16373
- Latch-up performance exceeds 500 mA
- ESD performance: Human-body model > 2000V Machine model > 200V
 - Charged-device model > 1000V
- Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA) (Preliminary)

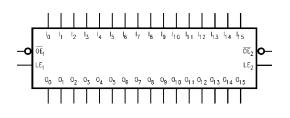
Ordering Code:

FAIRCH SEMICONDU 74LVT163 Low Volta with 3-ST	стоя 373 • 74L\ age 16-Bit	Transpare	January 1999 Revised June 2005
General Des The LVT16373 and ing latches with 3-S oriented application flip-flops appear tra Enable (LE) is HIGH the setup time is la the Output Enable outputs are in a higl The LVTH16373 da the need for exter inputs. These latches are applications, but wir face to a 5V environ are fabricated with achieve high spee maintaining a low per	LVTH16373 contair STATE outputs and its. The device is biansparent to the de I. When LE is LOW, thched. Data appear (OE) is LOW. Whe in impedance state. ata inputs include bian rnal pull-up resisto designed for low- th the capability to pro- ment. The LVT163 an advanced Bicf d operation similar	is intended for bus yte controlled. The ta when the Latch the data that meets s on the bus when n \overline{OE} is HIGH, the rushold, eliminating rs to hold unused voltage (3.3V) V _{CC} provide a TTL inter- 73 and LVTH16373 MOS technology to	 Features Input and output interface capability to systems at 5V V_{CC} Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH16373), also available without bushold feature (74LVT16373) Live insertion/extraction permitted Power Up/Power Down high impedance provides glitch-free bus loading Outputs source/sink -32 mA/+64 mA Functionally compatible with the 74 series 16373 Latch-up performance exceeds 500 mA ESD performance: Human-body model > 2000V Machine model > 200V Charged-device model > 1000V Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA) (Preliminary)
Ordering Co Order Number 74LVT16373GX (Note 1) 74LVT16373MEA (Note 2) 74LVT16373MTD (Note 2)	Dde: Package Number BGA54A (Preliminary) MS48A MTD48	[TAPE and REEL] 48-Lead Small Shrink	Package Description II Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide & Outline Package (SSOP), JEDEC MO-118, 0.300" Wide Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide
(Note 2) 74LVTH16373GX (Note 1) 74LVTH16373MEA (Note 2) 74LVTH16373MTD (Note 2)	BGA54A (Preliminary) MS48A MTD48	[TAPE and REEL] 48-Lead Small Shrink	II Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide Coutline Package (SSOP), JEDEC MO-118, 0.300" Wide Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide

Note 1: BGA package available in Tape and Reel only.

Note 2: Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

Logic Symbol



Connection Diagrams Pin Assignment for SSOP and TSSOP - LE₁ ŌĒ1 48 47 - I₀ 00-01. 46 - I₁ GND • 45 — GND 02 44 - I₂ 03 43 •13 42 - v_{cc} V_{CC} 41 0, - 1<u>4</u> 05 40 - I₅ GND 10 39 - GND 06 38 - I₆ 37 07 12 - I₇ 36 13 08 - 1₈ 35 09 14 - 1₉ GND · 15 34 - GND 010 16 33 - 4 o 32 17 011 - 4 1 31 18 - v_{cc} V_{CC} 19 30 012 - I_{1 2} 20 29 0₁₃ · - 4 3 GND・ 21 28 — GND 27 014 22 - 4₄ 0₁₅ · 23 26 - I₁₅ 0E2 25 24 - LE2 Pin Assignment for FBGA 1 2 3 4 5 6 ◄ ш υ 000000 000000 ш 000000 ш 000000 G 000000 т 000000 000000 (Top Thru View)

Pin Descriptions

Pin Names	Description
0E _n	Output Enable Input (Active LOW)
LEn	Latch Enable Input
I ₀ -I ₁₅	Inputs
O ₀ -O ₁₅	3-STATE Outputs
O ₀ –O ₁₅ NC	No Connect

FBGA Pin Assignments

	1	2	3	4	5	6
Α	O ₀	NC	OE ₁	LE ₁	NC	I ₀
В	0 ₂	0 ₁	NC	NC	I ₁	l ₂
С	O ₄	O ₃	V _{CC}	V _{CC}	l ₃	I ₄
D	0 ₆	O ₅	GND	GND	I ₅	I ₆
E	0 ₈	0 ₇	GND	GND	۱ ₇	I ₈
F	O ₁₀	O ₉	GND	GND	l ₉	I ₁₀
G	O ₁₂	O ₁₁	V _{CC}	V _{CC}	I ₁₁	I ₁₂
Н	0 ₁₄	0 ₁₃	NC	NC	I ₁₃	I ₁₄
J	O ₁₅	NC	OE ₂	LE ₂	NC	I ₁₅

Truth Tables

	Inputs		Outputs
LE ₁	OE ₁	I ₀ –I ₇	0 ₀ –0 ₇
Х	Н	Х	Z
Н	L	L	L
н	L	н	н
L	L	Х	O _o
	Outputs		
LE ₂	OE ₂	I ₈ –I ₁₅	0 ₈ –0 ₁₅
LE ₂ X	OE ₂	I ₈ −I ₁₅ ×	0 ₈ -0 ₁₅ Z
Х		X	

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial Z = HIGH Impedance

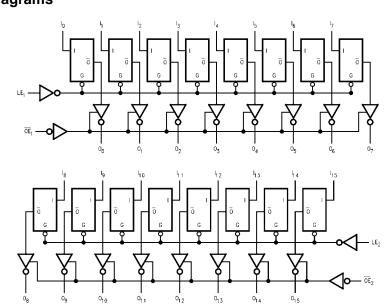
 $O_o =$ Previous output prior to HIGH-to-LOW transition of LE

Functional Description

The LVT16373 and LVTH16373 contain sixteen D-type latches with 3-STATE standard outputs. The device is byte controlled with each byte functioning identically, but independent of the other. Control pins can be shorted together to obtain full 16-bit operation. The following description applies to each byte. When the Latch Enable (LE_n) input is HIGH, data on the D_n enters the latches. In this condition the latches are transparent, i.e., a latch output will change states each time its D input changes. When LE_n is LOW,

Logic Diagrams

the latches store information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE_n. The 3-STATE standard outputs are controlled by the Output Enable (\overline{OE}_n) input. When \overline{OE}_n is LOW, the standard outputs are in the 2-state mode. When \overline{OE}_n is HIGH, the standard outputs are in the high impedance mode but this does not interfere with entering new data into the latches.



Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Symbol	Parameter	Value	Conditions	Uni
V _{CC}	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		١
Vo	DC Output Voltage	-0.5 to +7.0	Output in 3-STATE	١
		-0.5 to +7.0	Output in HIGH or LOW State (Note 4)	``
I _{IK}	DC Input Diode Current	-50	V _I < GND	m
I _{ОК}	DC Output Diode Current	-50	V _O < GND	m
I _O	DC Output Current	64	V _O > V _{CC} Output at HIGH State	
		128	V _O > V _{CC} Output at LOW State	m
I _{CC}	DC Supply Current per Supply Pin	±64		m
I _{GND}	DC Ground Current per Ground Pin	±128		m
T _{STG}	Storage Temperature	-65 to +150		°(

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage	2.7	3.6	V
/	Input Voltage	0	5.5	V
ОН	HIGH Level Output Current		-32	mA
OL	LOW Level Output Current		64	mA
Γ _A	Free-Air Operating Temperature	-40	85	°C
∆t/∆V	Input Edge Rate, V _{IN} = 0.8V–2.0V, V _{CC} = 3.0V	0	10	ns/V

Note 3: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied. Note 4: I_Q Absolute Maximum Rating must be observed.

DC Electrical Characteristics

Symbol	Parameter		V _{cc}	T _A = -40°0	C to +85°C	Units	Conditions
Symbol	Parameter		(V)	Min	Max	Units	Conditions
V _{IK}	Input Clamp Diode Voltage		2.7		-1.2	V	I _I = -18 mA
VIH	Input HIGH Voltage		2.7-3.6	2.0		V	$V_0 \le 0.1V$ or
VIL	Input LOW Voltage		2.7-3.6		0.8	V	$V_O \ge V_{CC} - 0.1V$
V _{OH}	Output HIGH Voltage		2.7-3.6	V _{CC} - 0.2			I _{OH} = -100 μA
			2.7	2.4		V	I _{OH} = -8 mA
			3.0	2.0			I _{OH} = -32 mA
V _{OL}	Output LOW Voltage		2.7		0.2		I _{OL} = 100 μA
			2.7		0.5		I _{OL} = 24 mA
			3.0		0.4	V	I _{OL} = 16 mA
			3.0		0.5		I _{OL} = 32 mA
			3.0		0.55		I _{OL} = 64 mA
I _{I(HOLD)}	Bushold Input Minimum Drive		3.0	75		μA	$V_I = 0.8V$
(Note 5)			5.0	-75		μΛ	$V_I = 2.0V$
I _{I(OD)}	Bushold Input Over-Drive		3.0	500		μA	(Note 6)
(Note 5)	Current to Change State		5.0	-500		μΑ	(Note 7)
l _l	Input Current		3.6		10		$V_I = 5.5V$
	Ī	Control Pins	3.6		±1	μA	$V_I = 0V \text{ or } V_{CC}$
		Data Pins	3.6		-5	μΑ	$V_I = 0V$
		Data Filis	5.0		1		$V_I = V_{CC}$
I _{OFF}	Power Off Leakage Current		0		±100	μA	$0V \leq V_{I} \text{ or } V_{O} \leq 5.5V$
I _{PU/PD}	Power Up/Down 3-STATE		0–1.5V		±100		$V_{O} = 0.5V$ to 3.0V
	Output Current		0-1.50		±100	μA	$V_I = GND \text{ or } V_{CC}$
I _{OZL}	3-STATE Output Leakage Curre	nt	3.6		-5	μA	$V_0 = 0.5V$
I _{OZH}	3-STATE Output Leakage Curre	nt	3.6		5	μA	V _O = 3.0V
I _{OZH} +	3-STATE Output Leakage Curre	nt	3.6		10	μA	$V_{CC} < V_O \le 5.5V$

DC Electrical Characteristics (Continued)

Symbol	Parameter	V _{cc}	V_{CC} $T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units	Conditions
	Falameter	(V)	Min	Max	Units	conditions
I _{CCH}	Power Supply Current	3.6		0.19	mA	Outputs HIGH
I _{CCL}	Power Supply Current	3.6		5	mA	Outputs LOW
I _{CCZ}	Power Supply Current	3.6		0.19	mA	Outputs Disabled
I _{CCZ⁺}	Power Supply Current	3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V,$
						Outputs Disabled
ΔI _{CC}	Increase in Power Supply Current	3.6		0.2	mA	One Input at V _{CC} – 0.6V
	(Note 8)					Other Inputs at V _{CC} or GND

Note 5: Applies to bushold versions only (74LVTH16373).

Note 6: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 7: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 8: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 9)

Symbol	Parameter	Vcc	T _A = 25°C			Units	Conditions	
Cymbol	i uluitotoi	(V)	Min	Тур	Max	onno	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF}\textbf{,}~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		0.8		V	(Note 10)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8		V	(Note 10)	

Note 9: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 10: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

AC Electrical Characteristics

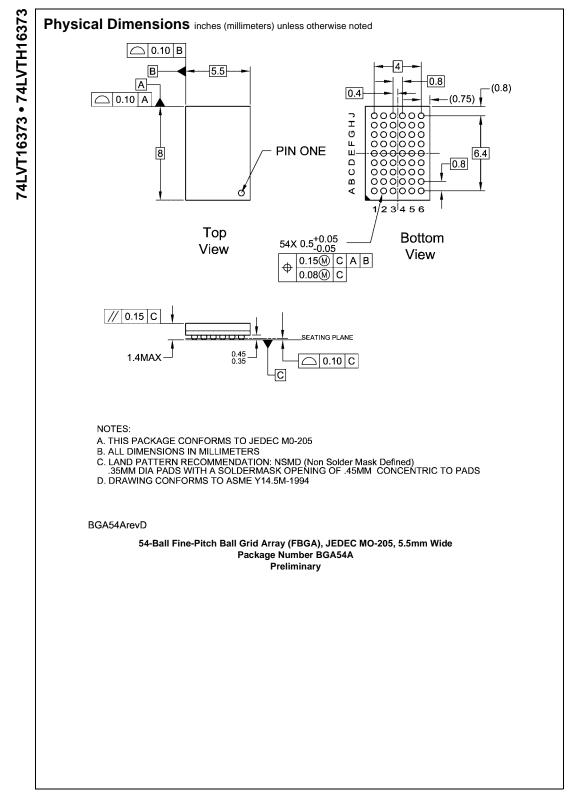
		TA				
Symbol	Parameter	V _{CC} = 3	$.3V \pm 0.3V$	V _{CC} = 2.7V		Units
		Min	Max	Min	Max	
t _{PHL}	Propagation Delay	1.5	3.9	1.5	4.3	ns
t _{PLH}	D _n to O _n	1.5	3.8	1.5	4.2	115
t _{PHL}	Propagation Delay	1.9	4.2	1.9	4.4	ns
t _{PLH}	LE to O _n	1.6	4.3	1.6	4.8	115
t _{PZL}	Output Enable Time	1.3	4.3	1.3	4.9	
t _{PZH}		1.0	4.3	1.0	5.1	ns
t _{PLZ}	Output Disable Time	1.5	4.7	1.5	4.8	
t _{PHZ}		2.0	5.0	2.0	5.4	ns
t _S	Setup Time, D _n to LE	1.0		0.8		ns
t _H	Hold Time, D _n to LE	1.0		1.1		ns
t _W	LE Pulse Width	3.0		3.0		ns
t _{OSHL}	Output to Output Skew (Note 11)		1.0		1.0	
t _{OSLH}			1.0		1.0	ns

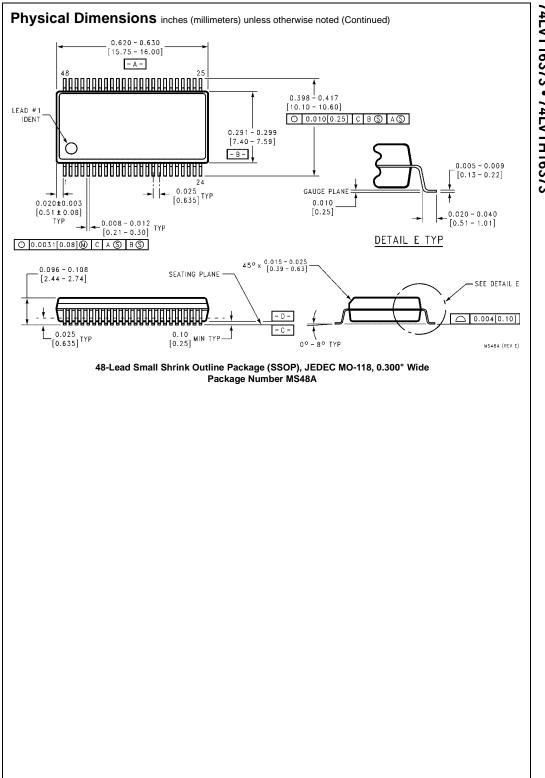
Note 11: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}).

Capacitance (Note 12)

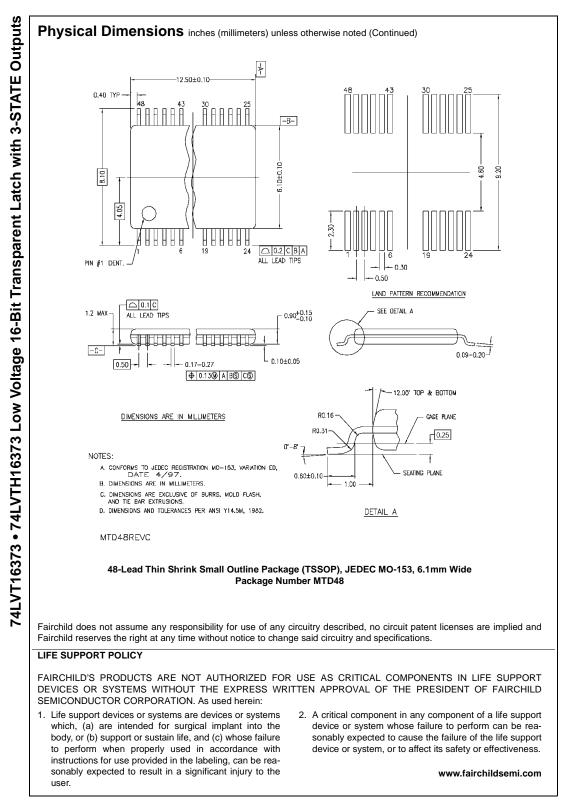
Symbol	Parameter	Conditions	Typical	Units	
C _{IN}	Input Capacitance	$V_{CC} = Open, V_I = 0V \text{ or } V_{CC}$	4	pF	
C _{OUT}	Output Capacitance	$V_{CC} = 3.0V$, $V_O = 0V$ or V_{CC}	8	pF	

Note 12: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012.





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